

Listing of Claims:

1-20. (Canceled)

1 21. (Original) A semiconductor structure comprising a silicon carbide epitaxial layer having a carrot defect which is terminated within the epitaxial layer.

2 22. (Original) A semiconductor structure comprising:
an off-axis silicon carbide substrate;
an epitaxial layer of silicon carbide on the substrate,
a carrot defect having a nucleation point in the vicinity of an interface between the substrate and the epitaxial layer, wherein the carrot defect terminates within the epitaxial layer.

3 23. (Original) A structure according to claim 22, wherein the substrate comprises silicon carbide having a polytype selected from the group consisting of 2H, 4H, and 6H.

4 24. (Original) A structure according to claim 22, wherein the silicon carbide substrate is cut off-axis towards the $\langle 11\bar{2}0 \rangle$ direction.

5 25. (Original) A structure according to claim 22, wherein the silicon carbide substrate is cut off-axis towards a crystallographic direction perpendicular to the c-axis.

6 26. (Original) A structure according to claim 22, wherein the epitaxial layer comprises a buffer layer.

X 27. (Original) A structure according to claim 22, wherein the epitaxial layer is doped with a dopant at a concentration of $1E18 \text{ cm}^{-3}$ or greater.

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8 28. (Original) A structure according to claim 27, wherein the dopant comprises nitrogen, phosphorus, boron or aluminum.

9 29. (Previously Presented) A structure according to claim 27 wherein the epitaxial layer is a first epitaxial layer, the structure further comprising:

a second epitaxial layer on the first epitaxial layer, the second epitaxial layer having fewer carrot defects therein than the first epitaxial layer.